Junkang Li

List of Publications by Year
in descending order

21	261	1040056 9	1058476 14
papers	citations	h-index	g-index

21	21	21	198
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Aggressive EOT Scaling of Ge pMOSFETs With HfO₂/AlO_{<italic>x</italic>}/GeO_{<italic>x</italic>} Gate-Stacks Fabricated by Ozone Postoxidation. IEEE Electron Device Letters, 2016, 37, 831-834.	3.0	50
2	Asymmetric Metal/Î±-In₂Se₃/Si Crossbar Ferroelectric Semiconductor Junction. ACS Nano, 2021, 15, 5689-5695.	14.6	36
3	Ultra fast (<1 ns) electrical characterization of self-heating effect and its impact on hot carrier injection in 14nm FinFETs. , 2017, , .		30
4	Quantitative Characterization of Interface Traps in Ferroelectric/Dielectric Stack Using Conductance Method. IEEE Transactions on Electron Devices, 2020, 67, 5315-5321.	3.0	23
5	BEOL Compatible Indium-Tin-Oxide Transistors: Switching of Ultrahigh-Density 2-D Electron Gas Over 0.8 Ã— 10¹⁴/cm² at Oxide/Oxide Interface by the Change of Ferroelectric Polarization. IEEE Transactions on Electron Devices, 2021, 68, 3195-3199.	3.0	20
6	High-Performance Germanium pMOSFETs With NiGe Metal Source/Drain Fabricated by Microwave Annealing. IEEE Transactions on Electron Devices, 2016, 63, 2665-2670.	3.0	16
7	Ionic Control over Ferroelectricity in 2D Layered van der Waals Capacitors. ACS Applied Materials & Interfaces, 2022, 14, 3018-3026.	8.0	16
8	Quantitative Characterization of Ferroelectric/Dielectric Interface Traps by Pulse Measurements. IEEE Transactions on Electron Devices, 2021, 68, 1214-1220.	3.0	14
9	First Experimental Demonstration of Robust HZO/Î²-Gaâ„Oâ‚ƒ Ferroelectric Field-Effect Transistors as Synaptic Devices for Artificial Intelligence Applications in a High-Temperature Environment. IEEE Transactions on Electron Devices, 2021, 68, 2515-2521.	3.0	14
10	Observation and Characterization of Recoverable Fatigue Process Under Low-Electric Field (<1.8MV/cm) in HfZrO Ferroelectric Film. IEEE Electron Device Letters, 2021, 42, 1288-1290.	3.9	10
11	The Impact of Channel Semiconductor on the Memory Characteristics of Ferroelectric Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2020, 8, 846-849.	2.1	8
12	Electrical Properties of Ge pMOSFETs With Ultrathin EOT HfO₂/AlO_{<italic>x</italic>}/GeO_{<italic>x</italic>} Gate-Stacks and NiGe Metal Source/Drain. IEEE Transactions on Electron Devices, 2017, 64, 4831-4837.	3.0	5
13	In-Situ Monitoring of Self-Heating Effect in Aggressively Scaled FinFETs and Its Quantitative Impact on Hot Carrier Degradation Under Dynamic Circuit Operation. , 2020, , .		5
14	Impact of Electrical Stress on Defect Generation in Thin GeO₂/Ge Gate Stacks Fabricated by Thermal Oxidation. IEEE Transactions on Electron Devices, 2020, 67, 2516-2521.	3.0	4
15	Effect of measurement speed (Î¼s-800 ps) on the characterization of reliability behaviors for FDSOI nMOSFETs. , 2018, , .		3
16	Ge CMOS technology with advanced interface and junction engineering. , 2018, , .		2
17	Thermal Stability Enhancement of NiGe Metal Source/Drain and Ge pMOSFETs by Dopant Segregation. IEEE Transactions on Electron Devices, 2019, 66, 5284-5288.	3.0	2
18	Traps Around Ge Schottky Junction Interface: Quantitative Characterization and Impact on the Electrical Properties of Ge MOS Devices. IEEE Journal of the Electron Devices Society, 2020, 8, 350-357.	2.1	2

#	Article	IF	Citations
19	Reduction of junction leakage current in Sub-10 nm ultra-shallow NiGe/n-Ge Schottky junctions by dopant segregation. , 2016, , .		1
20	NiGe metal source/drain Ge pMOSFETs for future high performance VLSI circuits applications. , 2017, , .		0
21	BEOL Compatible Indium-Tin-Oxide Transistors: Switching of Ultra-High-Density 2D Electron Gas over 0.8Ã—1014 /cm2 by Ferroelectric Polarization. , 2021, , .		0